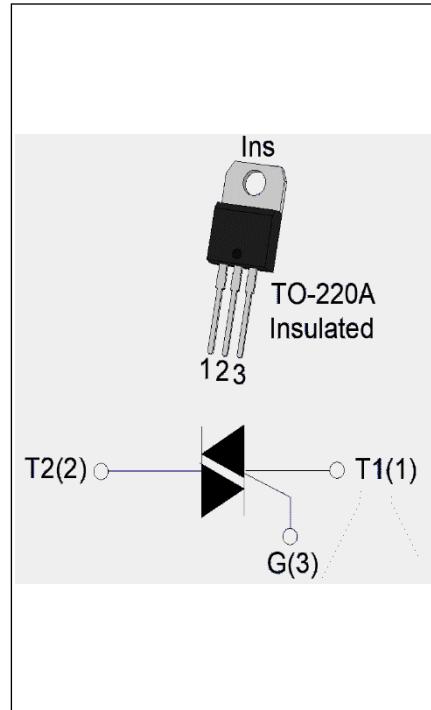




The JST24A-800C triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an internal ceramic pad, JST24A-800C provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\text{ I/II/III/IV}}$	25/25/25/50	mA



Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 79^\circ\text{C}$)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	250	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		275	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	340	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II III-IV	80 40	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W



Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.7)	V _{pp}	2	kV
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(T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33	I - II -III	MAX.	25	mA
		IV		50	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3K	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III-IV	MAX.	70	mA
		II		100	
I _H	I _T =500mA		MAX.	60	mA
dV/dt	V _D =540V Gate Open T _j =125°C		MIN.	500	V/μs
(dV/dt)c	(dI/dt)c=13.3A/ms, T _j =125°C		MIN.	6	V/μs
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25°C	TYP.	3	μs	
t _{off}			50		

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =35A t _p =380μs	T _j =25°C	1.5	V
V _{TO}	Threshold voltage	T _j =125°C	0.75	V
R _D	Dynamic resistance	T _j =125°C	18	m
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5	μA
I _{RRM}		T _j =125°C	2	mA

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	1.3	°C/W
R _{th(j-a)}	junction to ambient (AC)	60	°C/W



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FIG.1 Maximum power dissipation versus RMS on-state current

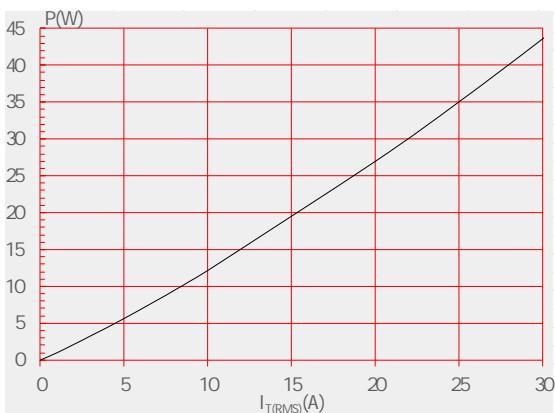


FIG.2: RMS on-state current versus case temperature

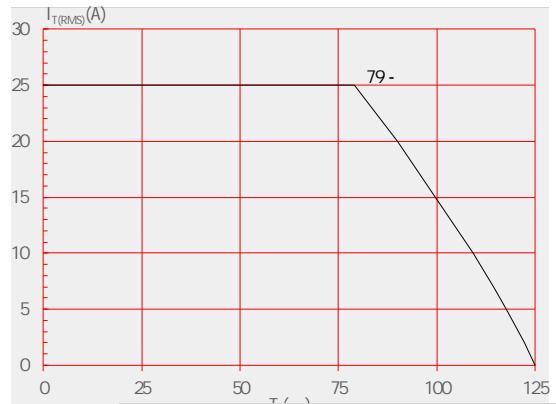


FIG.3: Surge peak on-state current versus number of cycles

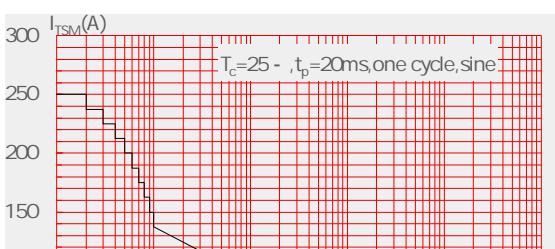
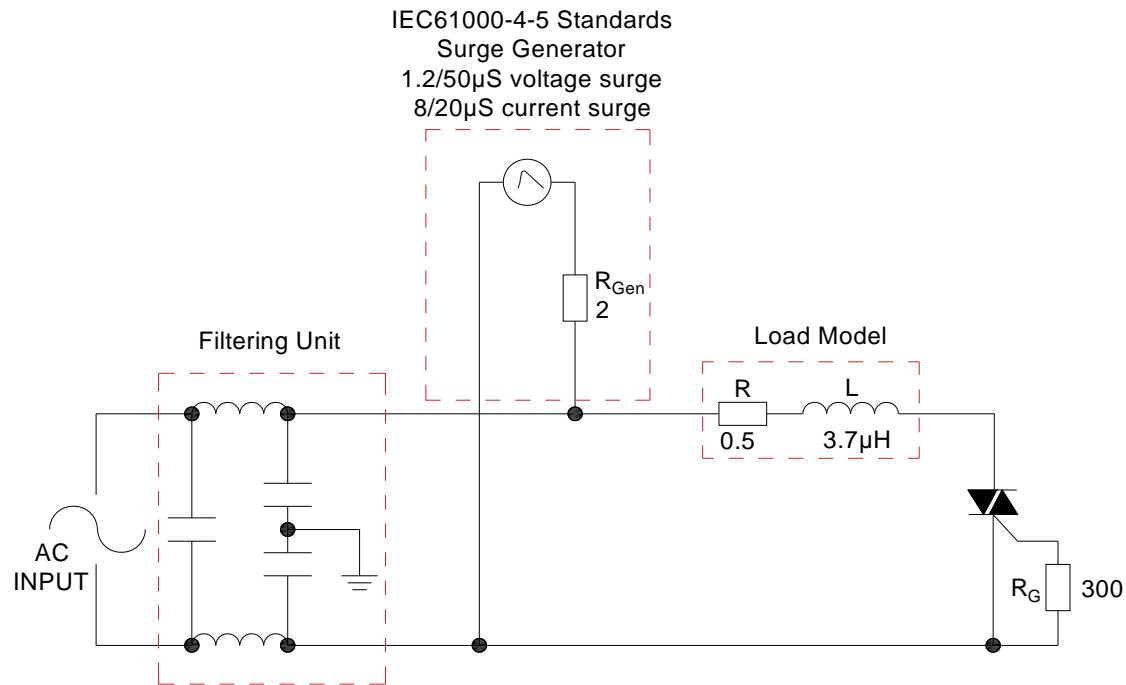


FIG.4: (



FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

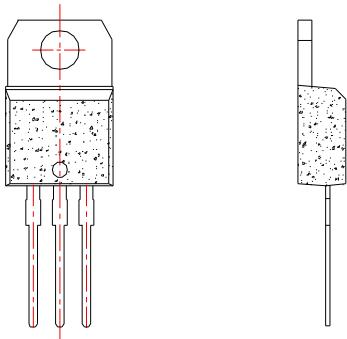
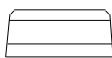




Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H	I			
JST24A-800C	800	25	50	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated





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